

**AMENDMENTS TO THE SPECIFICATION**

Please replace paragraph 28 of U.S. Patent Application Publication No. 2003/0046807 with the following paragraph:

The method of the present invention illustrated in the FIGS. 6-9 alleviates the problems associated with the previously described conventional techniques. The process begins, as with the conventional method, by depositing bottom shield 12, bottom half-gap 14, and SV stack 16. FIG. 6, which is a top view of MR reader 50 [[10]], illustrates the step of defining stripe height back edge 30. FIG. 6 shows second photoresist layer 28 selectively patterned on SV stack 16, leaving exposed a region of SV stack 16 behind desired stripe height back edge 30 to define stripe height back edge 30. MR reader 50 is milled and bottom half-gap 14 is revealed in the unprotected region. Thus, the first critical edge, stripe height back edge 30, is defined.